March 2007

Ultrafast recovery diode

Main product characteristics

I _{F(AV)}	1.5 A
V _{RRM}	200 V
T _j (max)	175° C
V _F (typ)	0.7 V
t _{rr} (typ)	15 ns

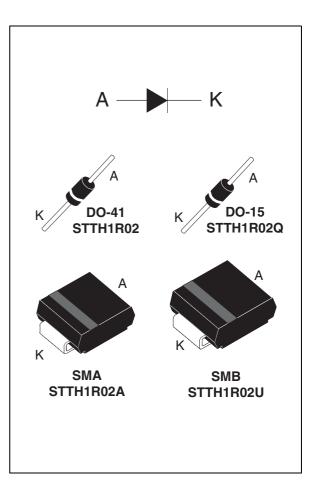
Features and benefits

- Very low conduction losses
- Negligible switching losses
- Low forward and reverse recovery times
- High junction temperature

Description

The STTH1R02 uses ST's new 200 V planar Pt doping technology, and it is specially suited for switching mode base drive and transistor circuits.

Packaged in DO-41, DO-15, SMA, and SMB, this device is intended for use in low voltage, high frequency inverters, free wheeling and polarity protection.



Order codes

Part Number	Marking
STTH1R02	STTH1R02
STTH1R02RL	STTH1R02
STTH1R02A	R1A
STTH1R02Q	STTH1R02Q
STTH1R02QRL	STTH1R02Q
STTH1R02U	1R2S

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1 Characteristics

Table 1.Absolute ratings (limiting values at $T_j = 25^{\circ}$ C, unless otherwise specified)

Symbol	Parameter	Value	Unit		
V _{RRM}	Repetitive peak reverse voltage	Repetitive peak reverse voltage			
I _{FRM}	Repetitive peak forward current	$\frac{DO-41^{(1)}}{DO-15^{(1)}} t_p = 5 \ \mu\text{s}, \ \text{F} = 5 \ \text{kHz}$ SMA / SMB		30	A
I _{F(RMS)}	RMS forward current	DO-41 / D SMA /SME		- 50	А
I _{F(AV)}	Average forward current, $\delta = 0.5$	DO-41 $T_{lead} = 110^{\circ} C$ DO-15 $T_{lead} = 110^{\circ} C$ SMA $T_c = 110^{\circ} C$ SMB $T_c = 110^{\circ} C$		1.5	A
I _{FSM}	Surge non repetitive forward current	60	А		
T _{stg}	Storage temperature range				°C
Тj	Maximum operating junction temperature	175	°C		

1. On infinite heatsink with 10 mm lead length

Table 2.Thermal parameters

Symbol		Parameter					
Р	Junction to lead	Load Longth - 10 mm on infinite bostoink	DO-41	45			
R _{th(j-l)}	Junction to lead	Lead Length = 10 mm on infinite heatsink	DO-15	45	°C/W		
Р	Junction to case		SMA	30	0/00		
R _{th(j-c)}	Junction to case		SMB	30			

Table 3. Static electrical characteristics

Symbol	Parameter	Test conditions		Min.	Тур	Max.	Unit
I _B ⁽¹⁾	Reverse leakage current	$T_j = 25^\circ C$	V _R = V _{RRM}			3	μA
'R'	Theverse leakage current	T _j = 125° C	VR − VRRM		2	20	μΑ
		$T_j = 25^\circ C$	I _F = 4.5 A			1.2	
V (2)	V _F ⁽²⁾ Forward voltage drop	$T_j = 25^\circ C$			0.89	1	v
VF		T _j = 100° C	l _F = 1.5 A		0.76	0.85	v
		T _j = 150° C			0.70	0.80	

1. Pulse test: t_p = 5 ms, δ < 2 %

2. Pulse test: t_p = 380 μ s, δ < 2 %

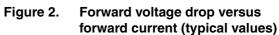
To evaluate the conduction losses use the following equation: P = 0.68 x $I_{F(AV)}$ + 0.08 ${I_F}^2_{(RMS)}$



Table 4.	Dynamic characteristics
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Symbol	Parameter	Test conditions	Min.	Тур	Max.	Unit
		$\label{eq:IF} \begin{array}{l} I_F = 1 \ A, \ dI_F/dt = -50 \ A/\mus, \\ V_R = 30 \ V, \ T_j = 25^\circ \ C \end{array}$		23	30	ns
t _{rr} Reverse recovery time	$\label{eq:lf} \begin{array}{l} I_F = 1 \mbox{ A, } dI_F/dt = -100 \mbox{ A/}\mu s, \\ V_R = 30 \mbox{ V, } T_j = 25^{\circ} \mbox{ C} \end{array}$		15	20	115	
I _{RM}	Reverse recovery current	I _F = 1.5 A, dI _F /dt = -200 A/µs, V _R = 160 V, T _j = 125° C		3	4	А
t _{fr}	Forward recovery time	I _F = 1.5 A, dI _F /dt = 100 A/μs V _{FR} = 1.1 x V _{Fmax} , T _j = 25° C		50		ns
V_{FP}	Forward recovery voltage	I_F = 1.5 A, dI _F /dt = 100 A/µs, T _j = 25° C		2.1		V





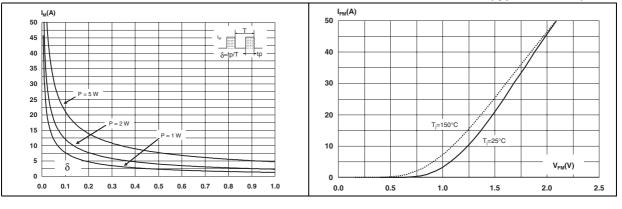
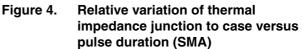


Figure 3. Forward voltage drop versus forward current (maximum values)



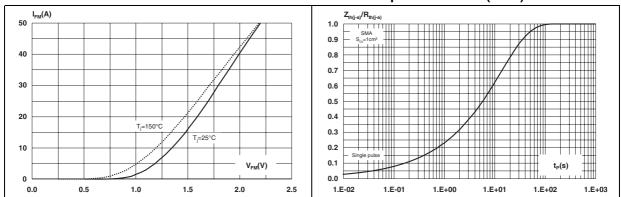
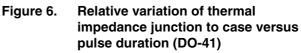


Figure 5. Relative variation of thermal impedance junction to case versus pulse duration (SMB)



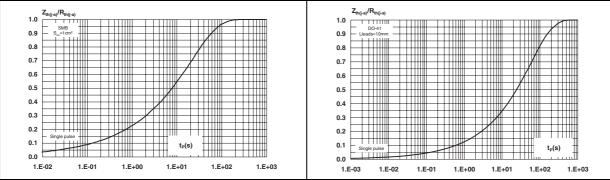


Figure 7. Relative variation of thermal impedance junction to case versus pulse duration (DO-15)

Figure 8. Junction capacitance versus reverse applied voltage (typical values)

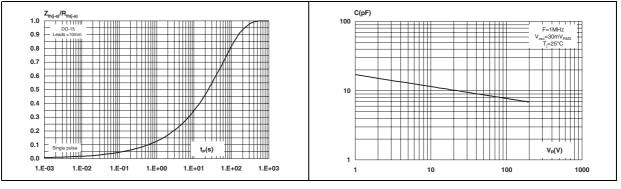


Figure 9. Reverse recovery charges versus dl_F/dt (typical values)

Figure 10. Reverse recovery time versus dl_F/dt (typical values)

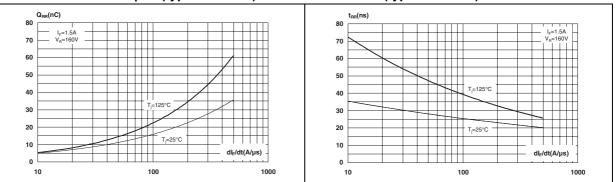
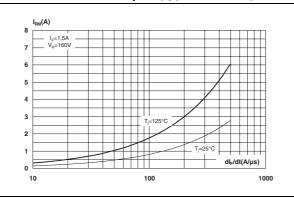


Figure 11. Peak reverse recovery curent versus dl_F/dt (typical values)



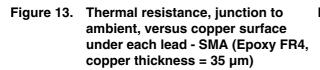


Figure 12. Dynamic parameters versus junction temperature

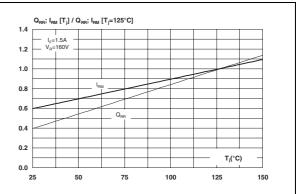
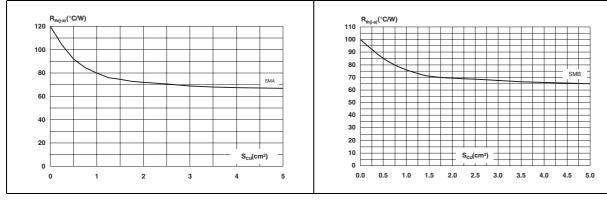
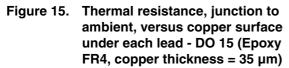
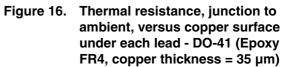
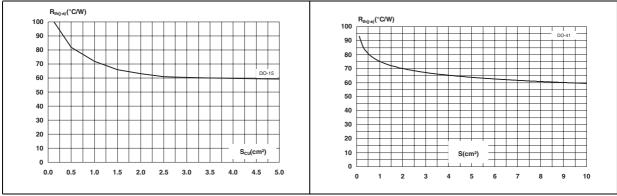


Figure 14. Thermal resistance, junction to ambient, versus copper surface under each lead - SMB (Epoxy FR4, copper thickness = 35 μm)

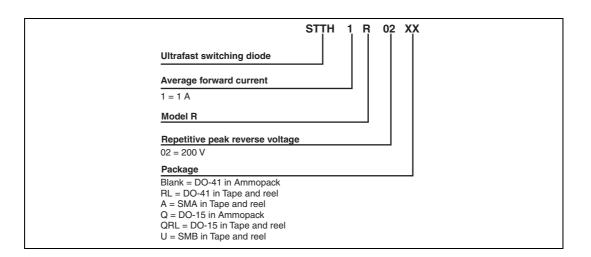








2 Ordering information scheme



3 Package information

• Epoxy meets UL94, V0

Table 5. DO-41 dimensions

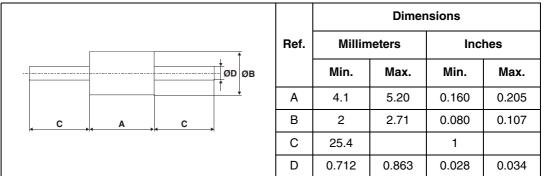
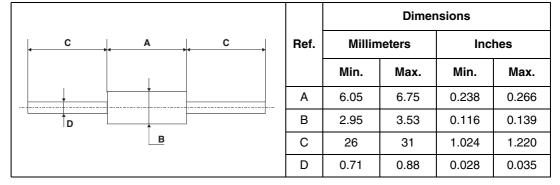


Table 6.DO-15 dimensions



				DIMEN	SIONS	
E1		REF.	Millim	neters	Inc	hes
			Min.	Max.	Min.	Max.
		A1	1.90	2.03	0.075	0.080
		A2	0.05	0.20	0.002	0.008
Е		b	1.25	1.65	0.049	0.065
	↑ (С	0.15	0.41	0.006	0.016
	A1	E	4.80	5.60	0.189	0.220
		E1	3.95	4.60	0.156	0.181
	b b	D	2.25	2.95	0.089	0.116
		L	0.75	1.60	0.030	0.063

Table 7.SMA dimensions

Figure 17. SMA footprint (dimensions in mm)

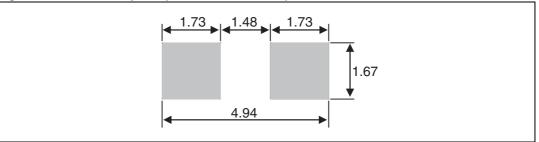
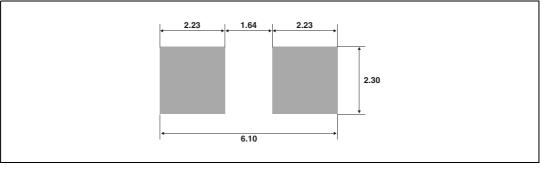




Table 8.SMB dimensions

				Dimer	nsions	
E1		Ref.	Millim	neters	Inc	hes
			Min.	Max.	Min.	Max.
		A1	1.90	2.45	0.075	0.096
		A2	0.05	0.20	0.002	0.008
		b	1.95	2.20	0.077	0.087
		с	0.15	0.41	0.006	0.016
	A1	Е	5.10	5.60	0.201	0.220
		E1	4.05	4.60	0.159	0.181
	l ∢ ▶	D	3.30	3.95	0.130	0.156
		L	0.75	1.60	0.030	0.063

Figure 18. SMB footprint (dimensions in mm)



In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com.



4 Ordering information

Part Number	Marking	Package	Weight	Base qty	Delivery mode	
STTH1R02	STTH1R02	DO-41	0.34 g	2000	Ammopack	
STTH1R02RL	STTH1R02	DO-41	0.34 g	5000	Tape and reel	
STTH1R02A	R1A	SMA	0.068 g	5000	Tape and reel	
STTH1R02Q	STTH1R02Q	DO-15	0.49 g	1000	Ammopack	
STTH1R02QRL	STTH1R02Q	DO-15	0.49 g	6000	Tape and reel	
STTH1R02U	1R2S	SMB	0.11 g	2500	Tape and reel	

5 Revision history

Date	Revision	Description of changes
03-May-2006	1	First issue
13-Oct-2006	2	Added DO-15 and SMB packages.
08-Mar-2007	3	Replaced Figure 8. Replaced e _{cu} with copper thickness.



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